

## isc Silicon PNP Power Transistor

# 2SA1166

### DESCRIPTION

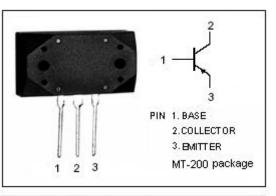
- Collector-Emitter Breakdown Voltage-V<sub>(BR)CEO</sub>= -150V(Min)
- Good Linearity of  $h_{\text{FE}}$
- High Power Dissipation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

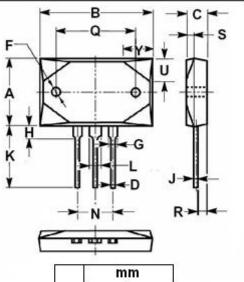
### **APPLICATIONS**

- Power amplifier applications
- Recommended for 100W high-fidelity audio frequency amplifier output stage

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-160	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-160	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
lc	Collector Current-Continuous	-15	А
Pc	Collector Power Dissipation @ $T_c$ =25°C	150	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C





DIM	MIN	MAX
A	21.00	21.70
В	35.80	36.70
С	5.60	6.20
D	1.04	1.07
F	3.10	3.50
G	1.90	2.40
н	3.60	4.00
J	0.55	0.85
κ	20.00	20.80
L	2.90	3.40
Ν	10.50	11.10
Q	24.00	24.50
R	2.90	3.30
S	2.00	2.20
Ű	6.90	7.10
Y	8.90	9.10

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### **ELECTRICAL CHARACTERISTICS**

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =-25mA; I <sub>B</sub> =0	-160			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =-1mA; I <sub>E</sub> =0	-160			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =-1mA; I <sub>C</sub> =0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.5A			-2.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.5A			-2.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -150V; I <sub>E</sub> = 0			-10	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-10	μA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -2A; V <sub>CE</sub> = -5V	55		160	
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f <sub>test</sub> = 1.0MHz		320		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -1A; V <sub>CE</sub> = -10V		60		MHz

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